

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 10-053495

(43)Date of publication of application : 24.02.1998

(51)Int.Cl.

C30B 29/38
C30B 23/00

(21)Application number : 09-094078

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(22)Date of filing : 11.04.1997

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(30)Priority

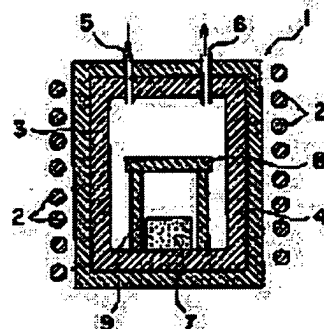
Priority number : 08141236 Priority date : 04.06.1996 Priority country : JP

(54) NITRIDE SINGLE CRYSTAL AND ITS PRODUCTION

(57)Abstract:

PROBLEM TO BE SOLVED: To produce a nitride single crystal having high quality to satisfy the characteristics for practical use and a sufficiently large size to enable the practical use as a bulk material and to provide a process for the easy and efficient production of the single crystal.

SOLUTION: A powdery mixture of a nitride powder and an oxide powder or a powdery amorphous nitride is used as a raw material powder 7 and heated in nitrogen atmosphere at a temperature lower than the sublimation temperature or the melting temperature of the nitride to effect the decomposition and evaporation of the nitride powder and the growth of the crystal of the decomposed and evaporated component from the vapor phase on a substrate 8. A large-sized nitride single crystal containing little impurity and having a dimension of e.g. ≥ 10 mm in length and width and $\geq 300\mu\text{m}$ thick or ≥ 20 mm long and $\geq 10\mu\text{m}$ diameter can be produced in a short time.



LEGAL STATUS

[Date of request for examination] 18.06.2003

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

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